

# **Connection Diagrams and Ordering Information**

Ambient Temperature	Туре	Package	Part Number	Packaging Type	Connection Diagram	
			SG1524BJ		INV. Input $\begin{bmatrix} 1 & 16 \end{bmatrix} V_{REF}$ N.I. Input $\begin{bmatrix} 2 & 15 \end{bmatrix} + V_{IN}$ OSC. Output $\begin{bmatrix} 3 & 14 \end{bmatrix} E$	
55°C to 125°C	J	Ceramic Dual Inline Package	SG1524BJ-883B	CERDIP	+C.L. Sense $\Box$ 4 13 $\Box$ C <sub>B</sub> -C.L. Sense $\Box$ 5 12 $\Box$ C <sub>A</sub>	
			SG1524BJ-DESC		$ \begin{array}{cccc}                                  $	
-25°C to 85°C	N	16-PIN Dual	SG2524BN		N Package: RoHS Compliant / Pb-	
0°C to 70°C		Package	SG3524BN	PDIP	free Transition DC: 0503 N Package: RoHS / Pb-free 100% Matte Tin Lead Finish	
-25°C to 85°C	DW	16-PIN Small	SG2524BDW	SOMB	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	
0°C to 70°C		Body Package	SG3524BDW	30008	DW Package: RoHS Compliant / Pb- free Transition DC: 0516 DW Package: RoHS / Pb-free 100% Matte Tin Lead Finish	
-55°C to		20-Pin Ceramic	SG1524BL-883B		1. N.C. 2. INV. Input 3. N.I. Input 4. OSC. Output 5. +C.L. Sense 6. N.C. 3. 2 1 20 19 11. N.C. 12. Comp 18 13. Shutdown 17 14. E <sub>A</sub> 15. C <sub>A</sub> 16. Io. N.C.	
125°C	L	Leadless Chip Carrier	SG1524BL	CLCC	7C.L. Sense 7 8. $R_{T}$ 8 9. $C_{T}$ 10. Ground 9 10 11 12 13 15 17. $C_{B}$ 14 18. $E_{B}$ 19. $+V_{IN}$ 20. $V_{REF}$	

Note:

1. Contact factory for DESC product availability.

All packages are viewed from the top.
 Hermetic Packages J, & L use Sn63/Pb37 hot solder lead finish, contact factory for availability of RoHS versions

4. Available in Tape & Reel. Append the letters "TR" to the part number. (i.e. SG3524BDW-TR)



## **Absolute Maximum Ratings**

Parameter	Value	Units
Input Voltage, (+V <sub>IN</sub> )	42	V
Collector Voltage	60	V
Logic Inputs	-0.3 to 5.5	V
Current Limit Sense Inputs	-0.3 to $V_{\text{IN}}$	V
Output Current (Each transistor)	200	mA
Reference Load Current	50	mA
Oscillator Charging Current	5	mA
Operating Junction Temperature		
Hermetic (J, L Packages)	150	°C
Plastic (N, DW Packages)	150	°C
Storage Temperature Range	-65 to 150	°C
Lead Temperature (Soldering, 10 seconds)	300	°C
RoHS Peak Package Solder Reflow Temp. (40 sec. max. exp.)	260 (+0, -5)	°C
Note: 1. Values beyond which damage may occur		

# **Thermal Data**

Parameter	Value	Units
J Package		·
Thermal Resistance-Junction to Case, $\theta_{JC}$	30	°C/W
Thermal Resistance-Junction to Ambient, $\theta_{JA}$	80	°C/W
N Package		
Thermal Resistance-Junction to Case, $\theta_{JC}$	40	°C/W
Thermal Resistance-Junction to Ambient, $\theta_{JA}$	65	°C/W
DW Package		
Thermal Resistance-Junction to Case, $\theta_{JC}$	40	°C/W
Thermal Resistance-Junction to Ambient, $\theta_{JA}$	95	°C/W
L Package		·
Thermal Resistance-Junction to Case, $\theta_{JC}$	35	°C/W
Thermal Resistance-Junction to Ambient, $\theta_{JA}$	120	°C/W
Note:		•

 Junction Temperature Calculation: T<sub>J</sub> = T<sub>A</sub> + (P<sub>D</sub> x θ<sub>JA</sub>).
 The above numbers for θ<sub>JC</sub> are maximums for the limiting thermal resistance of the package in a standard mounting configuration. The  $\theta_{JA}$  numbers are meant to be guidelines for the thermal performance of the device/pc-board system. All of the above assume no ambient airflow.



## Recommended Operating Conditions<sup>1</sup>

Parameter	Value	Units
Input Voltage (+V <sub>IN</sub> )	7 to 40	V
Collector Voltage	0 to 60	V
Error Amp Common Mode Range	2.3 to $V_{\text{REF}}$	V
Current Limit Sense Common Mode Range	0 to $V_{\text{IN}}$ - 2.5V	V
Output Current (Each transistor)	0 to 100	mA
Reference Load Current	0 to 20	mA
Oscillator Charging Current	25 to 1.8	μA / mA
Oscillator Frequency Range	100 to 400	Hz / kHz
Oscillator Timing Resistor (R <sub>T</sub> )	2 to 150	kΩ
Oscillator Timing Capacitor (C <sub>T</sub> )	1 to 0.1	nF/µF
Operating Ambient Temperature Range		
SG1524B	-55 to 125	°C
SG2524B	-25 to 85	°C
SG3524B	0 to 70	°C
Note: 1 Range over which the device is functional	•	

### **Electrical Characteristics**

(Unless otherwise specified, these specifications apply over the operating ambient temperatures for SG1524B with -55°C  $\leq$  T<sub>A</sub>  $\leq$  125°C, SG2524B with -25°C  $\leq$  T<sub>A</sub>  $\leq$  85°C, SG3524B with 0°C  $\leq$  T<sub>A</sub>  $\leq$  70°C, and +V<sub>IN</sub> = 20V. Low duty cycle pulse testing techniques are used that maintains junction and case temperatures equal to the ambient temperature.)

Devenuetor	Tost Conditions	SG	SG1524B/2524B			SG3524			
Parameter	Test conditions	Min.	Тур.	Max	Min.	Тур.	Max	Units	
Reference Section <sup>1</sup>	Reference Section <sup>1</sup>								
Output Voltage	T <sub>J</sub> = 25°C	4.95	5.00	5.05	4.90	5.00	5.10	V	
Line Regulation	$V_{IN} = 7V$ to $40V$		3	20		3	30	mV	
Load Regulation	I∟= 0 to 20mA		5	30		5	50	mV	
Temperature Stability <sup>5</sup>	Over Operating Temperature Range		15	50		15	50	mV	
Total Output Voltage Range	Over Line, Load and Temperature	4.90		5.10	4.80		5.20	V	
Short Circuit Current	V <sub>REF</sub> = 0V	25	50	120	25	50	120	mA	
Undervoltage Lockout Section									
Threshold Voltage		4.3	4.5	4.7	4.2	4.5	4.9	V	
Notes: 1. $I_L = 0mA$ 2. $E_L = -45$ hHz ( $B_L = 25$	$700 \circ C = 01.1E$								

2.  $F_{OSC} = 45 \text{ kHz} (R_T = 2700 \Omega, C_T = .01 \mu F)$ 3.  $V_{CM} = 2.3V \text{ to } V_{REF}$ 

4.  $V_{CM} = 0V \text{ to } 17.5V$ 

5. These parameters, although guaranteed over the recommended operating conditions, are not tested in production.

Parameter	<b>T</b>	SG1524B/2524B			SG3524B			
Parameter	Test Conditions	Min.	Тур.	Max	Min.	Тур.	Max	Units
Oscillator Section <sup>2</sup>			-	-				
Initial Accuracy	$T_J = 25^{\circ}C$	42	45	48	40	45	50	kHz
Voltage Stability	$V_{IN} = 7V$ to $40V$		0.1	1		0.1	1	%
Temperature Stability <sup>5</sup>	Over Operating Range		1	2		1	2	%
Minimum Frequency <sup>5</sup>	$R_{T} = 150 k\Omega, C_{T} = 0.1 \mu F$		50	140		50	120	Hz
Maximum Frequency	R <sub>T</sub> = 2 kΩ, C <sub>T</sub> = 470pF	400	600		400	600		kHz
Sawtooth Peak Voltage	V <sub>IN</sub> = 40V		3.5	3.9		3.5	3.9	V
Sawtooth Valley Voltage	$V_{IN} = 7V$	0.6	1		0.6	1		V
Clock Amplitude		3.0	4.0		3.0	4.0		V
Clock Pulse Width		0.2	0.5	1.2	0.2	0.5	1.2	μs
Error Amplifier Section	3							
Input Offset Voltage	Rs≤2kΩ		0.5	5		2	10	mV
Input Bias Current			1	5		1	10	μA
Input Offset Current				1			1	μA
DC Open Loop Gain	R <sub>L</sub> ≥ 10MΩ	60	78		60	78		dB
Output Low Level	I <sub>SINK</sub> = 100µA; V <sub>PIN 1</sub> - V <sub>PIN 2</sub> ≥ 150mV		0.2	0.5		0.2	0.5	V
Output High Level	I <sub>SOURCE</sub> = 100µA; V <sub>PIN 2</sub> - V <sub>PIN 1</sub> ≥ 150mV	3.8	4.2		3.8	4.2		V
Common Mode Rejection	$V_{CM}$ = 2.3V to $V_{REF}$	70	90		70	90		dB
Supply Voltage Rejection	$V_{IN} = 7V$ to 40V	76	100		76	100		dB
Gain-Bandwidth Product⁵	T <sub>J</sub> = 25°C	1	2		1	2		MHz
P.W.M. Comparator <sup>2</sup>								
Minimum Duty Cycle	$V_{COMP} = 0.5V$			0			0	%
Maximum Duty Cycle	V <sub>COMP</sub> = 3.9V	45	49		45	49		%
Current Limit Amplifier	Section <sup>4</sup>							
Sense Voltage		180	200	220	170	200	230	mV
Input Bias Current			-3	-10		-3	-10	μA
Notes:	1	1	1	1	1	1	1 1	

## Electrical Characteristics (continued)

1.  $I_L = 0mA$ 2.  $F_{OSC} = 45kHz (R_T = 2700 \ \Omega, C_T = .01 \mu F)$ 3.  $V_{CM} = 2.3V \text{ to } V_{REF}$ 4.  $V_{CM} = 0V \text{ to } 17.5V$ 5. These parameters, although guaranteed over the recommended operating conditions, are not tested in production.

Baramotor		SG1	SG1524B/2524B			G3524I			
	Test Conditions	Min.	Тур.	Max	Min.	Тур.	Max	Units	
Shutdown Input Sectio	Shutdown Input Section								
HIGH Input Voltage		2.0			2.0			V	
HIGH Input Current	$V_{SHUTDOWN} = 5V$		0.1	1		0.1	1	mA	
LOW Input Voltage				0.6			0.6	V	
Output Section (Each tra	ansistor)								
Collector Leakage Current	Vce = 60V			50			50	μA	
Collector Saturation	I <sub>C</sub> = 10mA		0.2	0.4		0.2	0.4	V	
Voltage	I <sub>C</sub> = 100mA		1.0	2.0		1.0	2.0	V	
	I <sub>E</sub> = 10mA	17.5	19		17.5	19		V	
Emilier Output Voltage	I <sub>E</sub> = 100mA	17	18		17	18		V	
Emitter Voltage Rise Time <sup>5</sup>	$R_E=2k\Omega,T_A=25^\circ C$		0.2	0.5		0.2	0.5	μs	
Collector Voltage Fall Time	$R_c = 2k\Omega$ , $T_A = 25^{\circ}C$		0.1	0.2		0.1	0.2	μs	
Power Consumption	Power Consumption								
Standby Current	$V_{IN} = 40V,$ $V_{SHUTDOWN} = 2.0 V$		5	12		5	12	mA	
Notes: 1. $L = 0mA$ 2. $F_{OSC} = 45kHz (R_T = 270)$ 3. $V_{CM} = 2.3V$ to $V_{REF}$ 4. $V_{CM} = 0V$ to 17.5V	$00\Omega, C_T = .01\mu F)$		1	1	1	1	1	1	

4.  $V_{CM} = 0V$  to 17.5V 5. These parameters, although guaranteed over the recommended operating conditions, are not tested in production.



## **Characteristic Curves**



Figure 2 · Oscillator Frequency vs. Timing Resistor and Capacitor  $V_{IN}$  = 20V,  $T_A$  = 25°C



Figure 3 - SG1524B Dead Times vs. Timing Capacitance ( $R_T = 2.7k\Omega$ )  $V_{IN} = 20V$ ,  $T_A = 25^{\circ}C$ 



Figure 4 · SG1524B Error Amp Voltage Gain vs. Freq Over  $R_F$ ;  $V_{IN}$  = 20V,  $T_A$  = 25°C

## Package Outline Dimensions

Controlling dimensions are in inches, metric equivalents are shown for general information.



Dim	MILLIM	ETERS	INCHES		
Dim	MIN	MAX	MIN	MAX	
А	1.35	1.75	0.053	0.069	
A1	0.10	0.25	0.004	0.010	
A2	1.25	1.52	0.049	0.060	
b	0.33	0.51	0.013	0.020	
с	0.19	0.25	0.007	0.010	
D	9.78	10.01	0.385	0.394	
E	5.79	6.20	0.228	0.244	
е	1.27	BSC	0.050 BSC		
н	3.81	4.01	0.150	0.158	
L	0.40	1.27	0.016	0.050	
Θ	0	8	0	8	
*LC		0.10		0.004	

\*Lead coplanarity

#### Note:

Dimensions do not include protrusions; these shall not exceed 0.155mm (.006") on any side. Lead dimension shall not include solder coverage.

Figure 5 - DW 16-Pin SOWB Package Dimensions



Dim	MILLIMETERS		INCHES		
Dim	MIN	MAX	MIN	MAX	
А	-	5.08	-	0.200	
A1	0.38	0.51	0.015	0.040	
A2	3.30	Тур.	0.13	0 Тур.	
b	0.38	0.51	0.015	0.020	
b2	0.76	1.52	0.030	0.060	
с	0.20	0.38	0.008	0.015	
D	18.54	20.57	0.730	0.810	
÷	2.54	BSC	0.10	BSC	
E1	6.10	6.60	0.240	0.260	
E	7.62	BSC	0.300	) BSC	
L	3.05		0.120		
θ	-	15°	-	15°	

### Note:

Dimensions do not include protrusions; these shall not exceed 0.155mm (.006") on any side. Lead dimension shall not include solder coverage.





Package	Outline	Dimensions
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Dim	MILLIM	ETERS	INC	HES
Dim	MIN	MAX	MIN	MAX
Α		5.08		0.200
b	0.38	0.51	0.015	0.020
b2	1.04	1.65	0.045	0.065
С	0.20	0.38	0.008	0.015
D	19.30	19.94	0.760	0.785
E	5.59	7.11	0.220	0.280
е	2.54	BSC	0.100 BSC	
eA	7.37	7.87	0.290	0.310
н	0.63	1.78	0.025	0.070
L	3.18	5.08	0.125	0.200
α	-	15°	-	15°
Q	0.51	1.02	0.020	0.040

Note:

Dimensions do not include protrusions; these shall not exceed 0.155mm (.006") on any side. Lead dimension shall not include solder coverage.

Figure 7 - J 16-Pin Ceramic Dual Inline Package Dimensions



Dim	MILLIM	ETERS	INC	HES	
Dim	MIN	MAX	MIN	MAX	
D/E	8.64	9.14	0.340	0.360	
E3	-	8.128	-	0.320	
е	1.270	BSC	0.050 BSC		
B1	0.635	TYP	0.02	5 TYP	
L	1.02	1.52	0.040	0.060	
А	1.626	2.286	0.064	0.090	
h	1.016	TYP	0.04	0 TYP	
A1	1.372	1.68	0.054	0.066	
A2	-	1.168	-	0.046	
L2	1.91	2.41	0.075	0.95	
B3	0.20	3R	0.0	08R	

#### Note:

All exposed metalized area shall be gold plated 60 micro-inch minimum thickness over nickel plated unless otherwise specified in purchase order.

Figure 8 - L 20-Pin Ceramic Leadless Chip Carrier (LCC) Package Outline Dimensions



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